

isc Silicon NPN Power Transistor

BU100

DESCRIPTION

- · Collector-Emitter Sustaining Voltage-
 - : V_{CEO(SUS)}= 60V(Min.)
- · Low Collector Saturation Voltage-
 - : V_{CE(sat)}= 3.3V(Max.)@ I_C= 8A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

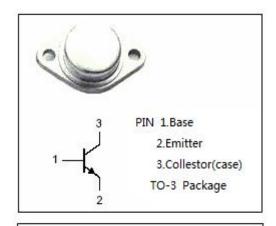


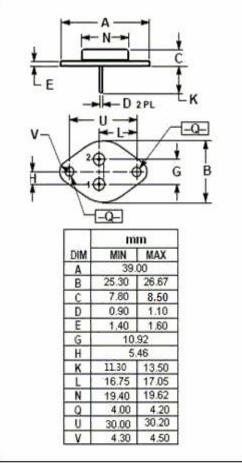
APPLICATIONS

 Designed for horizontal deflection output stage of CTV receivers and high voltage, fast switching and industrial applications.



| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|-------|------------|
| V _{CBO} | Collector-Base Voltage | 150 | V |
| V_{CEO} | Collector-Emitter Voltage | 60 | V |
| V_{EBO} | Emitter-Base Voltage | 7 | V |
| lc | Collector Current-Continuous | 10 | А |
| Ісм | Collector Current-Peak Repetitive | 15 | А |
| Pc | Collector Power Dissipation @ T _C =75°C | | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range -55~150 | | $^{\circ}$ |







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 50mA; I _B = 0 | 60 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 1mA; I _E = 0 | 150 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1mA; I _C = 0 | 7 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 8A; I _B = 2.5A | | | 3.3 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 8A; I _B = 2.5A | | | 2.2 | V |
| І _{СВО} | Collector Cutoff Current | V _{CB} = 120V; I _E = 0 | | | 10 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 7V; I _C = 0 | | | 10 | μА |
| h _{FE} | DC Current Gain | I _C = 2A; V _{CE} = 2V | 40 | | 90 | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = 0.5A; V _{CE} = 10V | 0.1 | | | MHz |

NOTICE:

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